

## Description

The SiT3901 is the industry's smallest and the lowest power digitally controlled MHz oscillator. With 0.4 mW of active power consumption at 6.78 MHz and 2.6 MHz output frequencies, this  $\mu Power$  oscillator enables longer battery life for consumer, IoT and wearable devices compared to a quartz-based oscillator or resonator.

The device comes in a small 1.5 mm x 0.8 mm package. The unique combination of ultra-low power, ultra-small package and flexible output frequency makes it ideal for power sensitive and space constrained applications.

## **Applications**

- Tablets
- Fitness bands
- Health and medical monitoring
- Wearables
- Portable audio
- Input devices
- IoT devices

#### **Features**

- Ultra-low current consumption of 105 μA at 2.6 MHz and 220 μA at 6.78 MHz
- ±50,000 ppm ±150,000 ppm pull range
- Ultra-small 1.5 mm x 0.8 mm package
- 2.6 MHz and 6.78 MHz with 6 decimal places of accuracy
- Operating temperature from -40°C to 85°C
- Frequency stability as low as ±50 ppm
- Programmable output drive strength for best
   EMI or driving multiple loads
- Ultra-light weight of 1.28 mg
- RoHS and REACH compliant, PFAS-free, Pbfree, Halogen-free and Antimony-free



## **Electrical Specifications**

#### Table 1. Electrical Characteristics for 6.78 MHz output

All Min and Max limits are specified over temperature and rated operating voltage with 15 pF output load unless otherwise stated. Typical values are at 25°C and nominal supply voltage.

Parameters	Symbol	Min.	Тур.	Max.	Unit	Condition		
				equency Ran	ge			
Output Frequency Range	f	_	6.78	-	MHz	Contact SiTime for other frequencies up to 26 MHz		
Frequency Stability and Aging								
nitial Tolerance f_tol -6,000 - +6,000 ppm Frequency offset at 25°C post reflow								
Frequency Stability	f_stab	-100	ı	+100	ppm	Inclusive of variations over operating temperature -20°C to +70°C or -40°C to +85°C, rated power supply voltage and output load.		
		-50	-	+50	ppm	Inclusive of variations over operating temperature -20°C to +70°C, rated power supply voltage and output load.		
Pull Range	PR	-50,000	-	+50,000				
First Year Aging	f_1year	-3	-	+3	ppm	At 25°C		
			Operatin	g Temperatu	reRange			
Operating Temperature Range	T_use	-20	-	+70	°C	Extended Commercial		
		-40	-	+85	°C	Industrial. Contact SiTime for -40°C to 105°C option.		
		Su	pply Voltage	and Curren	t Consump	otion		
Supply Voltage	VDD	1.62	1.8	1.98	V			
		2.25	-	3.63	V	Any voltage from 2.25 to 3.63 V		
Current Consumption[1]	IDD	-	220	270	μΑ	f = 6.78 MHz, any voltage, no load		



Table 1. Electrical Characteristics for 6.78 MHz (continued)

			-		-	
Parameters	Symbol	Min.	Тур.	Max.	Unit	Condition
			LVCMOS	Output Char	acteristics	5
Duty Cycle	DC	45	_	55	%	
Rise/Fall Time <sup>[3]</sup>	T_r, T_f	1	4	8	ns	Vdd = 1.8 V, 20% - 80%. Contact SiTime for other programmable rise/fall options
		ı	_	8	ns	Vdd = 2.25 V to 3.63 V, 20% - 80%. Contact SiTime for other programmable rise/fall options
Output High Voltage	VOH	90%	_	-	VDD	IOL = 0.5 mA (Vdd = 1.8 V)
						IOL = 1.2 mA (Vdd = 2.25 V to 3.63 V)
Output Low Voltage	VOL	-	_	10%	VDD	IOL = 0.5 mA (Vdd = 1.8 V)
						IOL = 1.2 mA (Vdd = 2.25 V to 3.63 V)
			Inpu	ıt Characteri	stics	
Input High Voltage	VIH	80%	_	_	VDD	
Input Low Voltage	VIL	Ī	_	20%	VDD	
Input Slew Rate	In-slew	10	_	_	V/µs	
Input Pull-down Impedance	Z_in	300	_	-	kΩ	Active mode (DP/OE pin = HIGH), Vdd = 1.8 V
		270	-	-	kΩ	Active mode (DP/OE pin = HIGH), Vdd = 2.25 V to 3.63 V
		2.5	_	-	$M\Omega$	Output disabled (DP/OE pin = LOW), Vdd = 1.8 V
		1.3	_	_	МΩ	Output disabled (DP/OE pin = LOW), Vdd = 2.25 V to 3.63 V
	•	S	tartup, Sta	ndby and Re	sume Timi	ing
Startup Time	T_start	-	75	150	ms	Measured from the time VDD reaches 90% of its final value
Enable Time	T_disable	-	_	20	μs	Measured from the time OE pin crosses 50% threshold
Disable Time	T_enable	-	2	3	ms	Measured from the time OE pin crosses 50% threshold
Standby Time	T_stdby	-	_	20	μs	Measured from the time ST pin crosses 50% threshold
Resume Time	T_resume	-	2	3	ms	Measured from the time ST pin crosses 50% threshold
				Jitter		
RMS Period Jitter	T_jitt	-	80	130	ps	f = 6.78 MHz, any voltage
RMS Phase Jitter	T_phj	_	1.5	2.5	ns	f = 6.78 MHz, any voltage, Integration bandwidth = 100 Hz to 40 kHz <sup>[2]</sup>

#### Notes:

- Current consumption with load is a function of the output frequency and output load. For any given output frequency, the capacitive loading will increase current consumption equal to C\_load\*VDD\*f(MHz).
   Max spec inclusive of 25 mV peak-to-peak sinusoidal noise on VDD. Noise frequency 100 Hz to 20 MHz.



#### Table 2. Electrical Characteristics for 2.6 MHz

All Min and Max limits are specified over temperature and rated operating voltage with 15 pF output load unless otherwise stated. Typical values are at 25°C and nominal supply voltage.

Parameters	Symbol	Min.	Тур.	Max.	Unit	Condition
			Fre	equency Ran	ge	<del>-</del>
Output Frequency Range	F_nom	_	2.6	-	MHz	Contact SiTime for other frequencies up to 26 MHz
			Frequen	cy Stability a	nd Aging	
Initial Tolerance	f_tol	-3,500	Ī	+3,500	ppm	Frequency offset at 25°C post reflow
Frequency Stability	f_stab	-100	ı	+100	ppm	Frequency offset relative to 25°C. Inclusive of variations over all operating temperatures, rated power supply voltage and output load.
		-50	-	+50	ppm	Frequency offset relative to 25°C. Inclusive of variations over operating temperature -20°C to +70°C, rated power supply voltage and output load.
Absolute Pull Range	PR	-150,000	-	+150,000	ppm	Relative to F_nom.
First Year Aging	f_1year	-3	_	+3	ppm	At 25°C
			Operatin	g Temperatu	reRange	
Operating Temperature Range	T_use	-20	_	+70	°C	Extended Commercial
		-40	_	+85	°C	Industrial. Contact SiTime for -40°C to 105°C option.
	•	Sur	oply Voltage	and Current	Consump	•
Current Consumption <sup>[3]</sup>	IDD	_	105	120	μA	Inclusive of ±150,000 ppm frequency pull range. Measured with no output load.
Supply Voltage	VDD	2.25	ı	3.63	٧	Any voltage from 2.25 to 3.63 V
			LVCMOS	Output Chara	acteristics	
Duty Cycle	DC	45	-	55	%	
Rise/Fall Time <sup>[4]</sup>	T_r, T_f	-	-	8	ns	$\label{eq:Vdd} Vdd = 2.25 \ V\ to\ 3.63 \ V,\ 20\% \ -\ 80\%. \ Contact\ SiTime\ for\ other programmable\ rise/fall\ options$
Output High Voltage	VOH	90%	-	_	VDD	IOH = -1.2 mA (Vdd = 2.25 V to 3.63 V)
Output Low Voltage	VOL	-	-	10%	VDD	IOL = 1.2 mA (Vdd = 2.25 V to 3.63 V)
			Inpu	ıt Characteris	stics	
Input High Voltage	VIH	80%	-	_	VDD	
Input Low Voltage	VIL	-	-	20%	VDD	
Input Slew Rate	In-slew	10	-	-	V/µs	
Input Pull-down Impedance	Z_in	270	_	_	kΩ	Active mode (ST pin = LOW), Vdd = 2.25 V to 3.63 V
		1.3	_	_	МΩ	Standby mode (ST pin =HIGH), Vdd = 2.25 V to 3.63 V
		5	Startup, Sta	ndby and Res	sume Timir	ng
Startup Time	T_start	_	75	150	ms	Measured from the time VDD reaches 90% of its final value
Enable Time	T_disable	-	-	20	μs	Measured from the time OE pin crosses 50% threshold
Disable Time	T_enable	-	2	3	ms	Measured from the time OE pin crosses 50% threshold
Standby Time	T_stdby	-	-	20	μs	Measured from the time ST pin crosses 50% threshold
Resume Time	T_resume	_	2	3	ms	Measured from the time ST pin crosses 50% threshold
		1		Jitter		·
RMS Period Jitter <sup>[5]</sup>	T_jitt	_	260	400	ps	f = 2.6 MHz, Vdd = 2.25 V to 3.63 V, Inclusive of ±150,000 ppm frequency pull range.
RMS Phase Jitter <sup>[5]</sup>	T_phj	-	1.5	2.5	ns	f = 2.6 MHz, Vdd = 2.25 V to 3.63 V, Integration bandwidth = 100 Hz to 40 kHz <sup>[2]</sup> , Inclusive of $\pm$ 150,000 ppm frequency pull range.

#### Notes:

- Current consumption with load is a function of the output frequency and output load. For any given output frequency, the capacitive loading will increase current consumption equal to C\_load\*VDD\*f(MHz).
   Max spec inclusive of 25 mV peak-to-peak sinusoidal noise on VDD. Noise frequency 100 Hz to 20 MHz.
- 5. Refer to the performance plot section for typical values at 2.5, 2.8, 3.0 and 3.3 V condition.



# **Table 3. Pin Description**

Pin	Symbol		Functionality
		Data Programming Pin	Tri-Level One Wire Interface: See "Frequency Control Protocol Description" section for programming details
			Active Low:
			L: Output driver is disabled
		Output	H: Specified output frequency
		Enable	Active High:
1	DP/OE/ST		H: Output driver is disabled
'			L: Specified output frequency
			Active Low:
			L: Output driver is disabled, device is in standby mode
			H: Specified output frequency
		Standby	Active High:
			H: Output driver is disabled, device is in standby mode
			L: Specified output frequency
2	OUT	Output	LVCMOS clock output
3	VDD	Power	Supply voltage. Bypass with a 0.01 µF X7R capacitor.
4	GND	Power	Connect to ground

## **Top View**

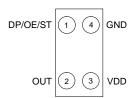


Figure 1. Pin Assignments



### **Table 4. Absolute Maximum Limits**

Attempted operation outside the absolute maximum ratings may cause permanent damage to the part. Actual performance of the IC is only guaranteed within the operational specifications, not at absolute maximum ratings.

Parameter	Test Condition	Value	Unit
Continuous Power Supply Voltage Range (VDD)		-0.5 to 3.63	V
Short Duration Maximum Power Supply Voltage (VDD)	<30 seconds	4.0	V
Continuous Maximum Operating Temperature		105	°C
Short Duration Maximum Operating Temperature	≤30 seconds	125	°C
Human Body Model (HBM) ESD Protection	JESD22-A115	2000	V
Charge-Device Model (CDM) ESD Protection	JESD22-C101	750	V
Machine Model (MM) ESD Protection	T <sub>A</sub> = 25°C	200	V
Latch-up Tolerance	J	ESD78 Compliant	
Mechanical Shock Resistance	MII 883, Method 2002	10,000	g
Mechanical Vibration Resistance	MII 883, Method 2007	70	g
1508 CSP Junction Temperature		150	°C
Storage Temperature		-65 to 150	°C
Soldering Temperature (follow standard Pb free soldering guidelines)	-	260	°C



## Description

SiT3901 device is a digitally controlled programmable oscillator (DCXO), which allows pulling the frequency around a nominal value dynamically. User can communicate with the device through a 1-pin tri-level serial interface. This device has two DCXO registers, which control the amount of frequency pull. Once the registers are set, the device sets its output frequency to a new value dynamically. The pull range is programmable to a maximum of ±50,000 ppm with a resolution of ±100 ppb. Writing into the DCXO registers does not cause any interruptions of output oscillations; the frequency will switch from one value to the new one smoothly.

### **Default Startup Condition**

The SiT3901 starts up at its factory programmed frequency. The DCXO registers values are initialized all zeros, effectively setting the frequency to the middle of the control range.

### **Frequency Control Protocol Description**

The device includes two DCXO registers. Data for each register is written to the device using a data frame.

#### **Data Frame Format**

Each frame consists of 40 bits. A frame has 2 parts:

- Register address, 24 bits
- Pull Frequency (PF) value represented as a 25-bit binary number
- The 25-bit Pull Frequency value is split over the data fields of two frames. One frame carries 9 most significant bits and the other frame carries the remaining 16 bits.



Figure 2. Data Frame

To control the output frequency, two frames per frequency update are required, and the frequency is only updated at the end of the second frame. The pull frequency value in this mode is 25 bits. This value is written to the device in two frames as Figure 4. Note that register (address: 0xFA0A2B) carries the most significant 9 bits as indicated by the XXXXXXXXX in Figure 3. The rest of the most significant bits must be set to 0.



**Figure 3. Frequency Control** 



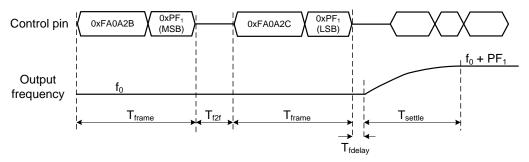


Figure 4. Frame Timing

## Frame Timing Parameters

### **Table 5. Frame Timing**

Parameter	Symbol	Min.	Max.	Unit
Frame Length	T <sub>frame</sub>	40	_	μS
Frame to Frame Delay	T <sub>f2f</sub>	2	_	μS
Frequency Settling Time	T <sub>settle</sub>	_	30	μS
Frame to Frequency Delay	T <sub>fdelay</sub>	_	8	μS

## **Calculating Pull Frequency Values**

The frequency pull value (PF) must be encoded as a 25-bit binary number representing the full scale range of the device.

The most significant 9 bits of the frequency pull value are written to the lowest nine bits of the data field at register address 0xFA0A2B. The 7 most significant bits of the data field are written to 0. The least significant 16 bits of the frequency pull value are written to the register address 0xFA0A2C.

Here are the steps to calculate the pull frequency (PF) value:

1. Find the pull frequency value using the equation below where "ppm" is the desired frequency offset from nominal.

Pull Frequency Value

PF (Pull Frequency Value)
6.78 MHz: PF (±50000 pull range) = 3.2544(1 + ppm/1e6)
2.6 MHz: PF (±150000 pull range) = 2.49875(1 + ppm/1e6)

For any frequency shifts (positive or negative PPM), convert the pull frequency value into a 25bit binary number.

#### Example 1

This example shows how to shift the frequency by +1000 ppm in a device with ±50000 pull range:

PF = 3.2544(1 + 1000/1e6)

Pull Value Integer = PF\*2^23

25 Bit Value = Pull Value Integer XOR (25165824)

MS Data Field = 000000000100000

LS Data Field = 1111101011010010

Frame for MS Word: 0xFA0A2B [MS Data Field]
Frame for LS Word: 0xFA0A2C [LS Data Field]

#### Example 2

This example shows how to shift the frequency by -25000 ppm in a device with ±50000 pull range:

PF = 3.2544(1 - 25000/1e6)

Pull Value Integer = PF\*2^23

25 Bit Value = Pull Value Integer XOR (25165824)

MS Data Field = 000000000010110 LS Data Field = 0010011000101101

Frame for MS Word: 0xFA0A2B [MS Data Field]

Frame for LS Word: 0xFA0A2C [LS Data Field]



### **Physical Interface**

The SiTime DCXO uses a serial input interface to adjust the pull frequency value.

The interface uses a one-wire tri-level return-to-middle signaling format. Figure 5 below shows the signal waveform of the interface.

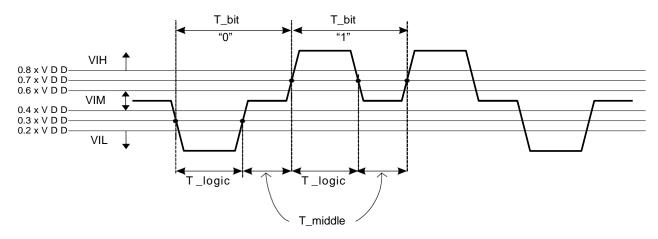


Figure 5. Serial 1-Wire Tri-Level Signaling

A logical bit "1" is defined by a high-logic followed by midlogic. A logical bit "0" is defined by a low-logic followed by mid-logic. The voltage ranges and time durations corresponding to low-logic, high-, and mid-logic are illustrated in Figure 5 and specified in electrical specification table.

The overall baud rate is computed as below:

$$baud\_rate = \frac{1}{T\_bit}$$

Figure 6 shows a simple circuit to generate tri-level circuit with a general purpose IO (GPIO) with tri-state capability. Most FPGAs and micro controllers/processors include such

GPIOs. If the GPIO does not support tri-state output, two IOs may be used in combination with external tri-state buffer to generate the tri-level signal; an example of such buffer is the SN74LVC1G126. The waveform at the output of the tri-state buffer is shown in Figure 5. When the GPIO drives Low or High voltage, the rise/fall times are typically fast (sub-5ns range). When the output is set to Hi-Z, the output settles at middle voltage with a RC response. The time constant is determined based on the total capacitance on frequency control pin and the parallel resistance of the pullup and pull-down resistors. The time constant in most practical situations will be less than 50ns; this necessitate choosing longer T\_middle to allow the RC waveform to settle within 5% or so.



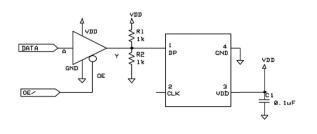


Figure 6. Circuit Diagram for Generating Tri-Level Signal with Tri-State Buffer

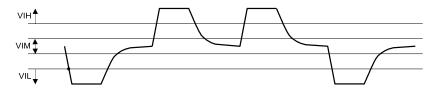


Figure 7. Tri-State Signal Generated with Tri-State Buffer

When using a tri-state buffer as shown above, care must be taken if the DATA and OE lines transition at the same time that there are no glitches. A glitch might occur, for example, if the OE line enables the output slightly before the data line has finished its logical transition. One way around this, albeit at the cost of some data overhead, is to use an extra OE cycle on every bit, as shown in Figure 8.

Note that the diagram assumes an SN74LVC125, which has a low-true OE/ line (output is enabled when OE/ is low). For a high-true OE part, such as the SN74LVC126, the polarity of that signal would be reversed.

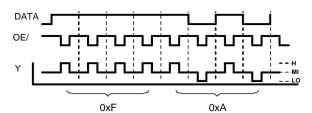


Figure 8. Signal Polarity



# **Block Diagram**

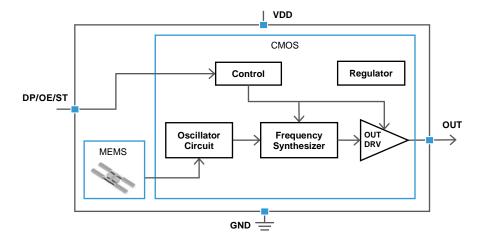


Figure 9. SiT3901 Block Diagram



## **Changing Device Operating Mode**

Upon power cycling, the device defaults to the digital programming mode; pin 1 exhibits DP functionality. Once in output enable (OE) or stand-by (ST) mode, the device must be power cycled to return to digital programming mode. Switching from the digital programming mode to the output enable or stand-by modes is done by writing to two specific separate registers described below. The mode will only change after both registers have been written to. For the both OE and ST modes two polarity options are available: active High and active Low.

The procedure to change to active Low OE mode is the following:

■ Write: 0xFA0A00 0040 (clear the DP pin receiver)

Write: 0xFA0A25 78D3 (switch function from DP to OE)

Write order	Register address	Data value
1	0xFA0A00	0x0040
2	0xFA0A25	0x78D3

The procedure to change to active High OE mode is the following:

■ Write: 0xFA0A00 0040 (clear the DP pin receiver)

Write: 0xFA0A25 7853 (switch function from DP to OE)

Write order	Register address	Data value
1	0xFA0A00	0x0040
2	0xFA0A25	0x7853

The procedure to change to active Low ST mode is the following:

■ Write: 0xFA0A00 0040 (clear the DP pin receiver)

Write: 0xFA0A25 78B3 (switch function from DP to ST)

Write order	Register address	Data value
1	0xFA0A00	0x0040
2	0xFA0A25	0x78B3

The procedure to change to active High ST mode is the following:

■ Write: 0xFA0A00 0040 (clear the DP pin receiver)

Write: 0xFA0A25 7833 (switch function from DP to ST)

Write order	Register address	Data value
1	0xFA0A00	0x0040
2	0xFA0A25	0x7833

### **Output Enable Mode**

Once the device's operation mode has been changed to the output enable mode, a high level on the DP/OE pin will enable the clock output for the active Low OE mode and vice versa for active High OE mode. A low level on the DP/OE pin will disable the output for active Low OE mode and high level will disable it for active high OE as per Table 6.

**Table 6. Operating Modes and Output States** 

DP/OE pin	Mode	Output	IDD Example		
LOW	Output Disabled	Hi-Z	45 μA @ 2.6 MHz		
HIGH	Output Enabled	Specified frequency	120 μA @ 2.6 MHz 270 μA @ 6.78 MHz		
	Active High				
HIGH	Output Disabled	Hi-Z	45 μA @ 2.6 MHz		
LOW	Output Enabled	Specified frequency	120 μA @ 2.6 MHz 270 μA @ 6.78 MHz		

## Stand-by mode

Once the device's operation mode has been changed to the stand-by mode, a high level on the DP/ST pin will enable the clock output for the active Low ST mode and vice versa for active High ST mode. A low level on the DP/ST pin will disable the output for active Low ST mode and high level will disable it for active high ST as per Table 7.

**Table 7. Operating Modes and Output States** 

DP/OE pin	Mode	Output	IDD Example		
	Active Low				
LOW	Output Disabled	Weak pull-down	1.5 μΑ		
HIGH	Output Enabled	Specified frequency	120 μA @ 2.6 MHz 270 μA @ 6.78 MHz		
	Active High				
HIGH	Output Disabled	Weak pull-up	1.5 µA		
LOW	Output Enabled	Specified frequency	120 μA @ 2.6 MHz 270 μA @ 6.78 MHz		



# **Test Circuit and Waveform**

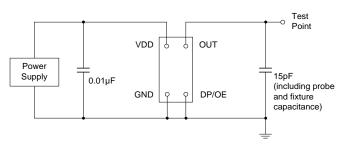


Figure 10. Test Circuit

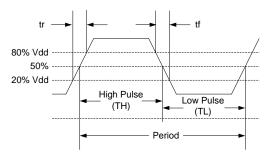


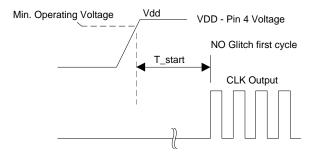
Figure 11. Waveform<sup>[6]</sup>

### Note:

6. Duty Cycle is computed as Duty Cycle = TH/Period.



## **Timing Diagram**



T\_start: Time to valid clock output from power on

Figure 12. Startup Timing[7]

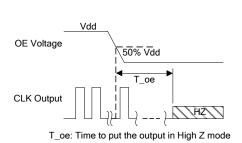
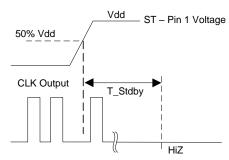


Figure 14. OE Disable Timing (OE Mode Only)

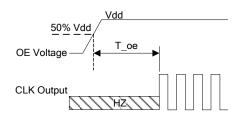


T\_Stdby: Time for output to go high-Z from the time ST pin crosses 50% threshold

Figure 16. Standby Timing[7]

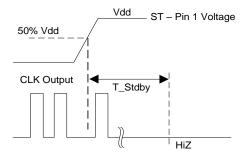
### Notes:

7. SiT3901 supports "no runt" pulses and "no glitch" output during startup or resume.



T\_oe: Time to re-enable the clock output

Figure 13. OE Enable Timing (OE Mode Only)

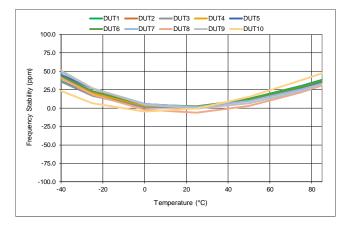


T\_Stdby: Time for output to go high-Z from the time ST pin crosses 50% threshold

Figure 15. Resume Timing<sup>[7]</sup>



# Performance Plots[8]



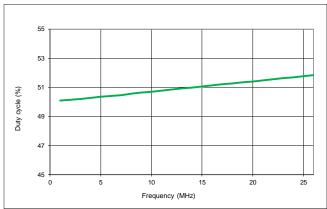


Figure 17. Frequency vs Temperature

Figure 18. Duty Cycle vs Frequency

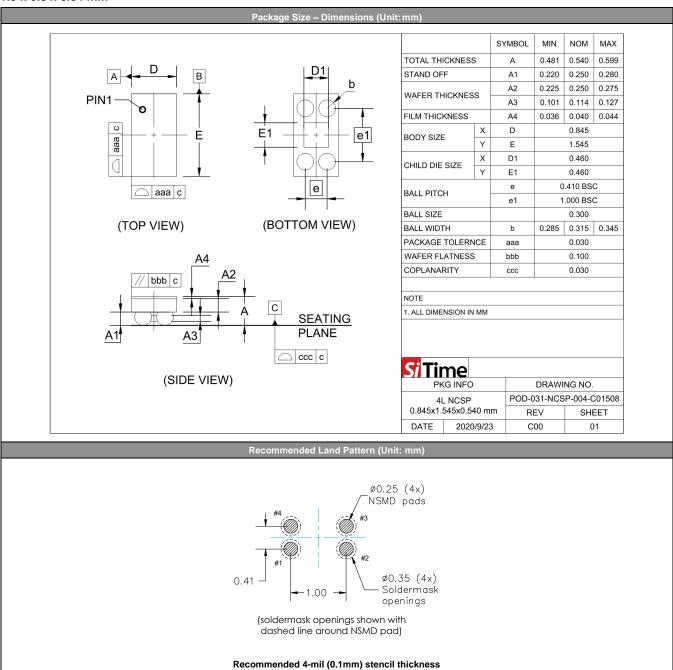
## Notes:

8. All data is measured at room temperature, unless otherwise stated.



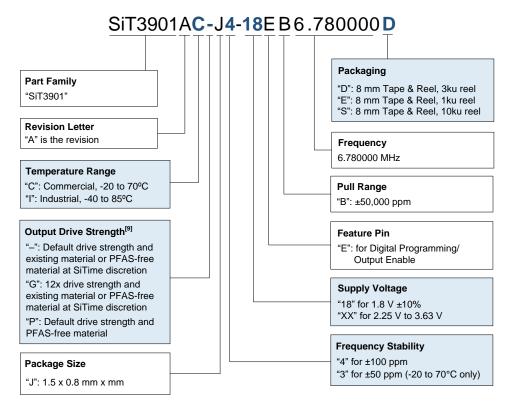
### **Dimensions and Patterns**

#### 1.5 x 0.8 x 0.54 mm





# **Ordering Information 6.78 MHz**

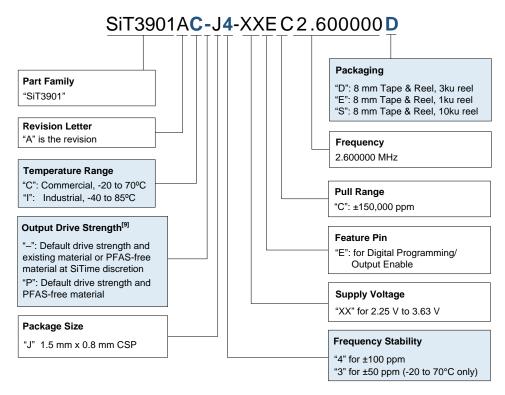


#### Notes:

9. Contact SiTime for other drive strength options that result in different rise/fall time for any given output load.



# **Ordering Information 2.6 MHz**





#### **Table 8. Revision History**

Version	Release Date	Change Summary
0.15	20-May-2020	Preliminary release
0.16	20-May-2020	Title updated Features section updated Table 2 updated
0.18	10-Jun-2020	Updated with programming information Fixed formatting
0.21	10-Sep-2020	Added pull range to ordering information Revised pull frequency equation and examples
0.23	22-Sep-2020	Removed IDD for unrelated output frequencies
0.25	8-Dec-2020	Updated output voltage high
0.27	8-Jul-2021	Added pull range to electrical specifications table, various updates to frequency control registers, and updated frequency stability condition, updated initial tolerance specification
0.29	29-Nov-2021	Added "G" ordering code option for 12x drive strength Resolved formatting errors in the input characteristics section of electrical specifications table
1.01	20-May-2022	Updated current consumption, phase jitter, and period jitter based on characterization data at 6.78 MHz Removed performance plots corresponding to current consumption, phase jitter, and period jitter Updated product description and features section
1.2	8-Nov-2024	Added option for 2.6 MHz. Updated with OE and ST mode. PFAS free ordering code update.

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